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In the version of this article initially published, the first entry in Table 2 referred to the carrier density of I_{\max} , which has since been deleted. The Fig. 3a caption, third sentence, contained “not at the same n_s ,” which has been removed, and the Fig. 3b caption starting “Benchmarking I_{sat} versus n ” has been altered to read “versus n_s .” Additionally, the Supplementary information has been updated after the phrase “carrier densities at which I_{min} is extracted” was removed from Note S1 and the Fig. S1 caption. The clarifications have been made in the HTML and PDF versions of the article.

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